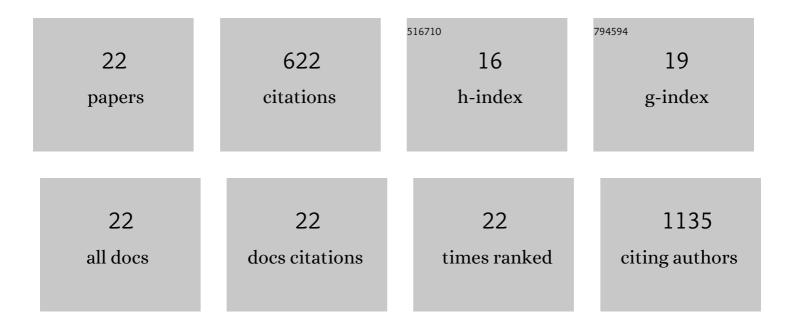
## Hae Jin Kim

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/11985767/publications.pdf Version: 2024-02-01



HAE LINEKIM

#	Article	IF	CITATIONS
1	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. Advanced Intelligent Systems, 2020, 2, 1900082.	6.1	36
2	Bipolar resistive switching property of Si <sub>3</sub> N <sub>4â^'x</sub> thin films depending on N deficiency. Journal of Materials Chemistry C, 2020, 8, 1755-1761.	5.5	4
3	Novel Selectorâ€Induced Currentâ€Limiting Effect through Asymmetry Control for Highâ€Density Oneâ€Selector–Oneâ€Resistor Crossbar Arrays. Advanced Electronic Materials, 2019, 5, 1800806.	5.1	10
4	Defect-Engineered Electroforming-Free Analog HfO <sub><i>x</i></sub> Memristor and Its Application to the Neural Network. ACS Applied Materials & Interfaces, 2019, 11, 47063-47072.	8.0	33
5	Singleâ€Cell Stateful Logic Using a Dualâ€Bit Memristor. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800629.	2.4	23
6	Nucleationâ€Limited Ferroelectric Orthorhombic Phase Formation in Hf <sub>0.5</sub> Zr <sub>0.5</sub> O <sub>2</sub> Thin Films. Advanced Electronic Materials, 2019, 5, 1800436.	5.1	55
7	Fabrication of a Cuâ€Coneâ€Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. Advanced Functional Materials, 2019, 29, 1806278.	14.9	51
8	Nociceptive Memristor. Advanced Materials, 2018, 30, 1704320.	21.0	116
9	Cu cone inserted CBRAM device fabrication and its improved switching reliability induced by field concentration effect. , 2018, , .		0
10	Investigation of the retention performance of an ultra-thin HfO2 resistance switching layer in an integrated memory device. Journal of Applied Physics, 2018, 124, .	2.5	24
11	Balancing the Source and Sink of Oxygen Vacancies for the Resistive Switching Memory. ACS Applied Materials & Interfaces, 2018, 10, 21445-21450.	8.0	21
12	Filament Shape Dependent Reset Behavior Governed by the Interplay between the Electric Field and Thermal Effects in the Pt/TiO <sub>2</sub> /Cu Electrochemical Metallization Device. Advanced Electronic Materials, 2017, 3, 1600404.	5.1	24
13	Doubleâ€Layerâ€Stacked One Diodeâ€One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> . Advanced Electronic Materials, 2017, 3, 1700152.	5.1	42
14	Stateful logic circuit and material using memristors. , 2017, , .		0
15	Roles of conducting filament and non-filament regions in the Ta <sub>2</sub> O <sub>5</sub> and HfO <sub>2</sub> resistive switching memory for switching reliability. Nanoscale, 2017, 9, 6010-6019.	5.6	22
16	Nextâ€Generation Memory: Double‣ayerâ€Stacked One Diodeâ€One Resistive Switching Memory Crossbar Array with an Extremely High Rectification Ratio of 10 <sup>9</sup> (Adv. Electron. Mater. 7/2017). Advanced Electronic Materials, 2017, 3, .	5.1	1
17	A study of the transition between the non-polar and bipolar resistance switching mechanisms in the TiN/TiO <sub>2</sub> /Al memory. Nanoscale, 2016, 8, 16455-16466.	5.6	22
18	Thickness effect of ultra-thin Ta2O5 resistance switching layer in 28 nm-diameter memory cell. Scientific Reports, 2015, 5, 15965.	3.3	51

Hae Jin Kim

#	Article	IF	CITATIONS
19	Thicknessâ€dependent electroforming behavior of ultraâ€thin Ta <sub>2</sub> O <sub>5</sub> resistance switching layer. Physica Status Solidi - Rapid Research Letters, 2015, 9, 362-365.	2.4	19
20	Surface-area-tuned, quantum-dot-sensitized heterostructured nanoarchitectures for highly efficient photoelectrodes. Nano Research, 2014, 7, 144-153.	10.4	25
21	Hierarchical assembly of TiO2–SrTiO3 heterostructures on conductive SnO2 backbone nanobelts for enhanced photoelectrochemical and photocatalytic performance. Journal of Hazardous Materials, 2014, 275, 10-18.	12.4	37
22	Multiâ€Level Control of Conductive Filament Evolution and Enhanced Resistance Controllability of the Cuâ€Cone Structure Embedded Conductive Bridge Random Access Memory. Advanced Electronic Materials, 0, , 2100209.	5.1	6